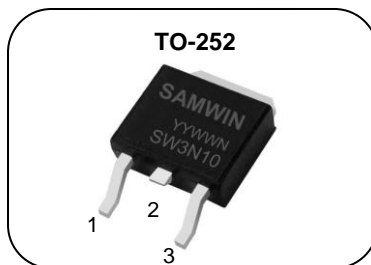


## N-channel D-PAK MOSFET

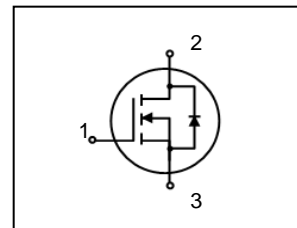
### Features

- High ruggedness
- $R_{DS(ON)}$  (Max 107m $\Omega$ )@ $V_{GS}=10V$
- Gate Charge (Typical 21nC)
- Improved dv/dt Capability
- 100% Avalanche Tested



1. Gate 2. Drain 3. Source

$BV_{DSS}$  : 100V  
 $I_D$  : 3A  
 $R_{DS(ON)}$  : 107m $\Omega$



### General Description

This power MOSFET is produced with advanced VDMOS technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics. This power MOSFET is usually used at high efficient DC to DC converter block and switch mode power supply.

### Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW D 3N10	SW3N10	TO-252	REEL

### Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain to Source Voltage	100	V
$I_D$	Continuous Drain Current (@ $T_C=25^\circ C$ )	3*	A
	Continuous Drain Current (@ $T_C=100^\circ C$ )	1.9*	A
$I_{DM}$	Drain current pulsed (note 1)	12	A
$V_{GS}$	Gate to Source Voltage	$\pm 16$	V
$E_{AS}$	Single pulsed Avalanche Energy (note 2)	187	mJ
$E_{AR}$	Repetitive Avalanche Energy (note 1)	40	mJ
dv/dt	Peak diode Recovery dv/dt (note 3)	5	V/ns
$P_D$	Total power dissipation (@ $T_C=25^\circ C$ )	44	W
	Derating Factor above 25 $^\circ C$	0.35	W/ $^\circ C$
$T_{STG}, T_J$	Operating Junction Temperature & Storage Temperature	-55 ~ + 150	$^\circ C$
$T_L$	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	$^\circ C$

\*. Drain current is limited by junction temperature.

### Thermal characteristics

Symbol	Parameter	Value	Unit
$R_{thic}$	Thermal resistance, Junction to case	2.84	$^\circ C/W$
$R_{thja}^*$	Thermal resistance, Junction to ambient (PCB Mount)		$^\circ C/W$
$R_{thia}$	Thermal resistance, Junction to ambient	80.2	$^\circ C/W$

\*. The value varied due to mounted PCB pad areas

## Electrical characteristic ( $T_C = 25^\circ\text{C}$ unless otherwise specified )

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
$BV_{DSS}$	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$		0.11		$V/^\circ\text{C}$
$I_{DSS}$	Drain to source leakage current	$V_{DS}=100V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=80V, T_C=125^\circ\text{C}$			50	$\mu A$
$I_{GSS}$	Gate to source leakage current, forward	$V_{GS}=16V, V_{DS}=0V$			11	$\mu A$
	Gate to source leakage current, reverse	$V_{GS}=-16V, V_{DS}=0V$			11	$\mu A$
<b>On characteristics</b>						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.5		2.5	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D = 3.5A$		85	107	$m\Omega$
$G_{fs}$	Forward Transconductance	$V_{DS} = 20 V, I_D = 1.5A$	6			S
<b>Dynamic characteristics</b>						
$C_{iss}$	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		1050		pF
$C_{oss}$	Output capacitance			65		
$C_{rss}$	Reverse transfer capacitance			40		
$t_{d(on)}$	Turn on delay time	$V_{DS}=50V, I_D=3A, R_G=25\Omega$ (note 4,5)		8	15	ns
$t_r$	Rising time			20	35	
$t_{d(off)}$	Turn off delay time			36	50	
$t_f$	Fall time			18	35	
$Q_g$	Total gate charge	$V_{DS}=80V, V_{GS}=10V, I_D=3A$ (note 4,5)		21	40	nC
$Q_{gs}$	Gate-source charge			3		
$Q_{gd}$	Gate-drain charge			5		

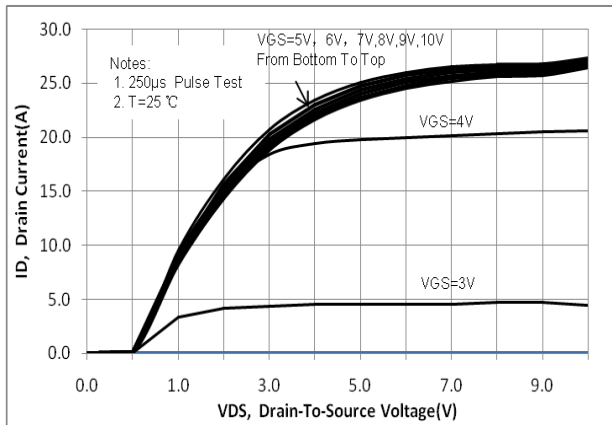
## Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			3	A
$I_{SM}$	Pulsed source current				12	A
$V_{SD}$	Diode forward voltage drop.	$I_S=3A, V_{GS}=0V$			1.5	V
$T_{rr}$	Reverse recovery time	$I_S=3A, V_{GS}=0V,$		28		ns
$Q_{rr}$	Breakdown voltage charge	$di_f/dt=100A/\mu s$		38		nC

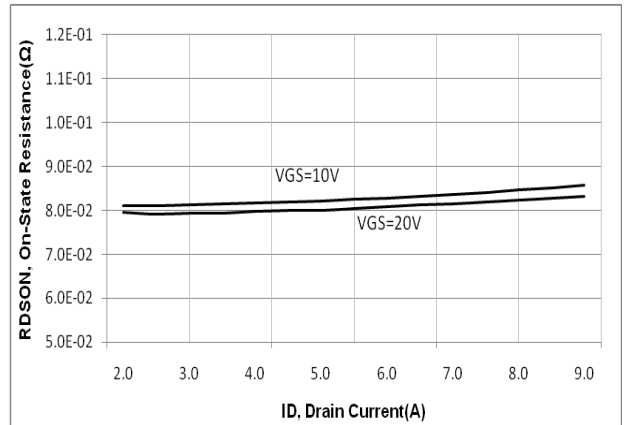
### ※. Notes

1. Repeative rating : pulse width limited by junction temperature.
2.  $L = 41.6\text{mH}, I_{AS} = 3A, V_{DD} = 50V, R_G=25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 3A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature.

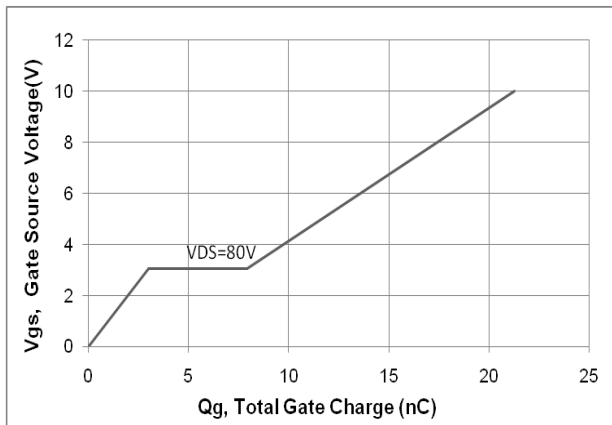
**Fig. 1. On-state characteristics**



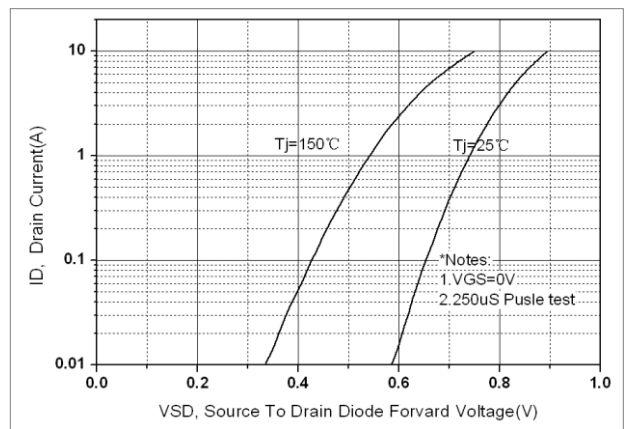
**Fig. 2. On-resistance variation vs. drain current and gate voltage**



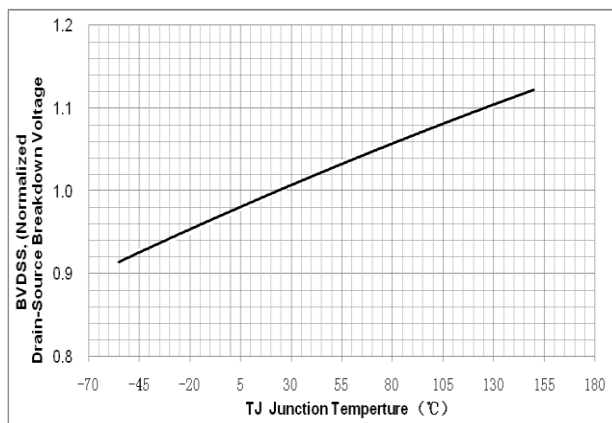
**Fig. 3. Gate charge characteristics**



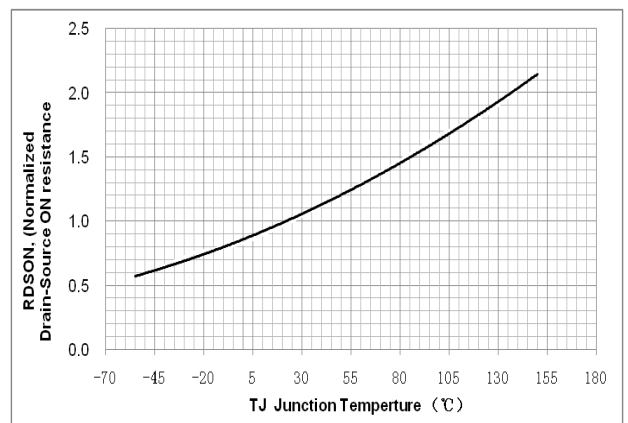
**Fig. 4. On state current vs. diode forward voltage**



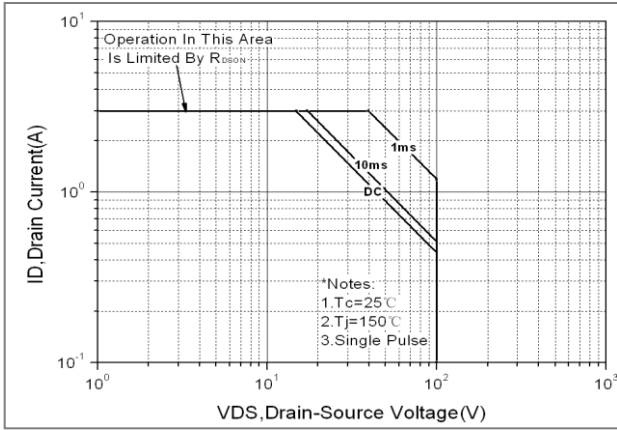
**Fig 5. Breakdown Voltage Variation vs. Junction Temperature**



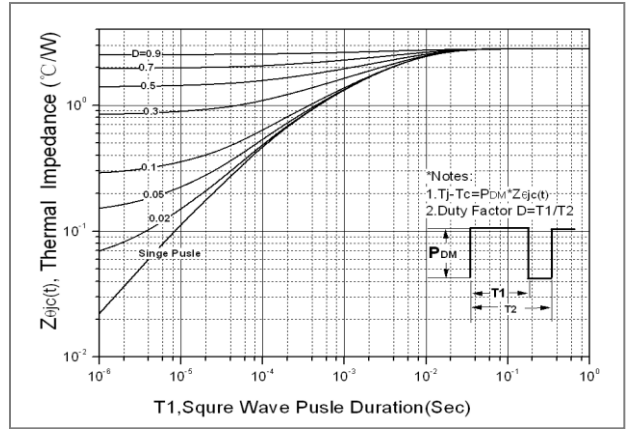
**Fig. 6. On resistance variation vs. junction temperature**



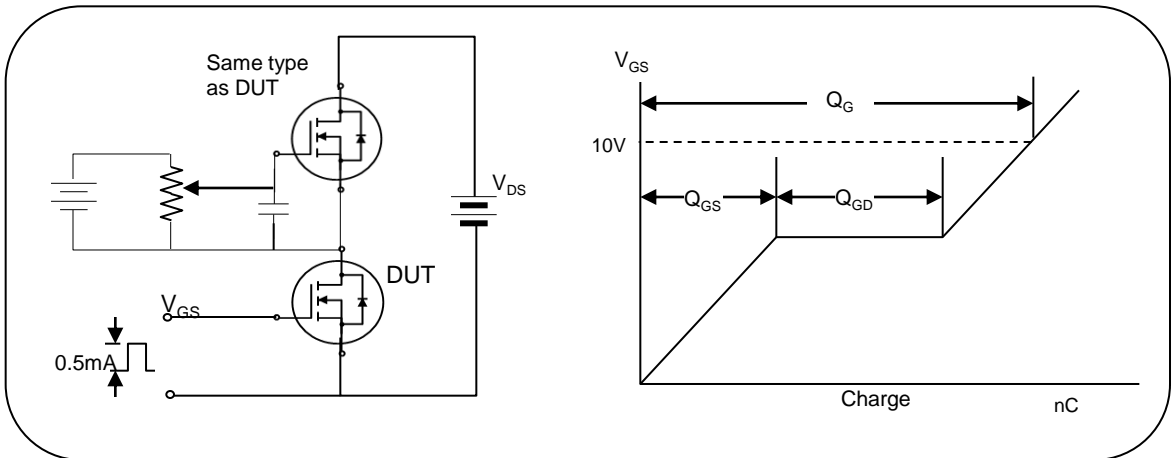
**Fig. 7. Maximum safe operating area**



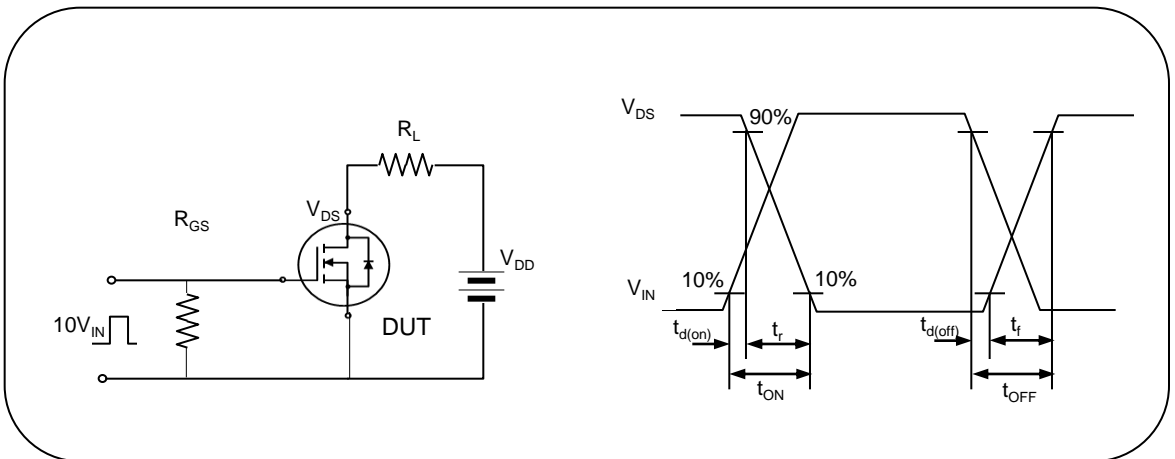
**Fig. 8. Transient thermal response curve**



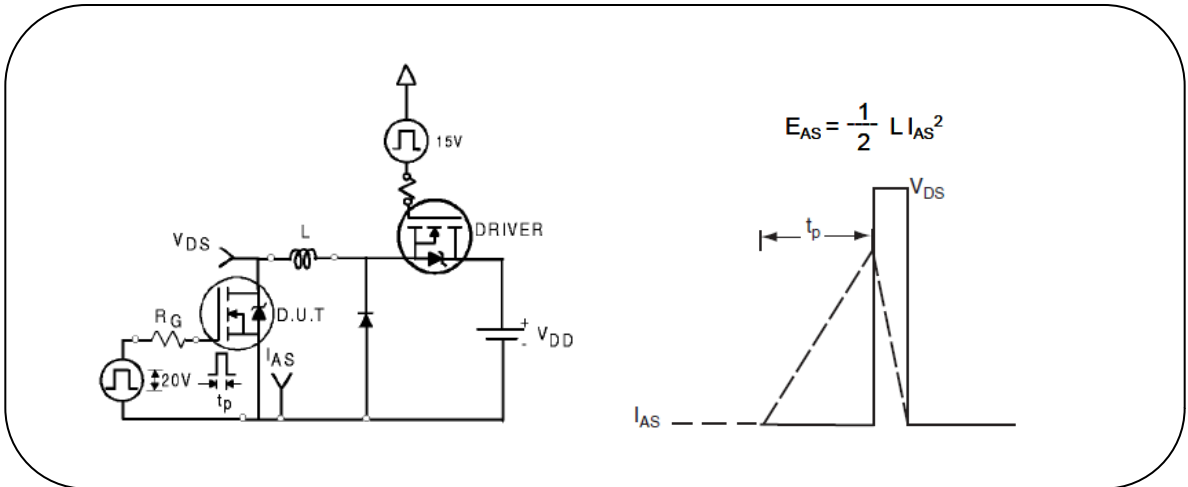
**Fig. 9. Gate charge test circuit & waveform**



**Fig. 10. Switching time test circuit & waveform**



**Fig. 11. Unclamped Inductive switching test circuit & waveform**



**Fig. 12. Peak diode recovery dv/dt test circuit & waveform**

